**Product data sheet** 

# 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO220 plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ( $T_{i(max)} = 150$  °C).

### 2. Features and benefits

- · High bidirectional blocking voltage capability
- High junction operating temperature capability
- · High thermal cycling performance
- · Planar passivated for voltage ruggedness and reliability
- · Very high current surge capability

# 3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- · Inrush protection
- Motor control
- Voltage regulation

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	800	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>mb</sub> ≤ 129 °C; <u>Fig. 1</u>	-	-	12.7	А
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>mb</sub> ≤ 129 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	20	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	210	А
		half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 8.3 \text{ ms}$	-	-	231	Α
T <sub>j</sub>	junction temperature		-	-	150	°C
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	-	4.5	32	mA
Dynamic	characteristics					,
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 402 V; T <sub>j</sub> = 150 °C;exponential waveform; gate open circuit	1000	-	-	V/µs
		$V_{\rm DM}$ = 536 V; $T_{\rm j}$ = 150 °C; ( $V_{\rm DM}$ = 67% of $V_{\rm DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs

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# **5. Pinning information**

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	}	A K G
3	G	gate		sym037
mb	A	mounting base; connected to anode		

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN20-800T	TO220	TYN20-800T,127	Tube	50	SOT78	13-Jun-2008

# 7. Marking

### Table 4. Marking codes

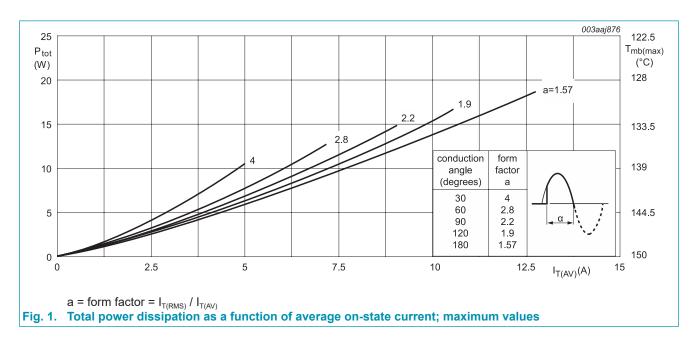
Type number	Marking codes				
	Assembly factory: d	Assembly factory: A			
TYN20-800T	TYN20 800T PJdxxxx xx	TYN20 800T PJAxxxx xx			

# 8. Limiting values

**Table 5. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$V_{RRM}$	repetitive peak reverse voltage		-	800	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>mb</sub> ≤ 129 °C; <u>Fig. 1</u>	-	12.7	А
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>mb</sub> ≤ 129 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	20	А
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	210	А
		half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 8.3 \text{ ms}$	-	231	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	220.5	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	5	А
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_GM$	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C



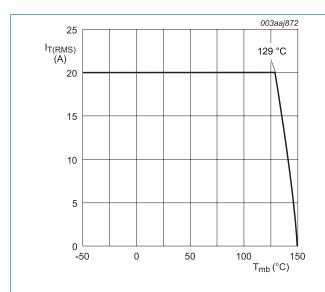
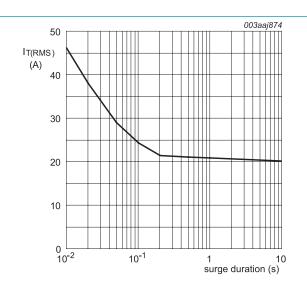
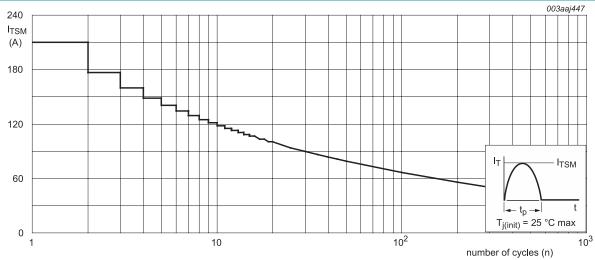


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T<sub>mb</sub> =129 °C Fig. 3. RMS on-state current as a function of surge duration; maximum values

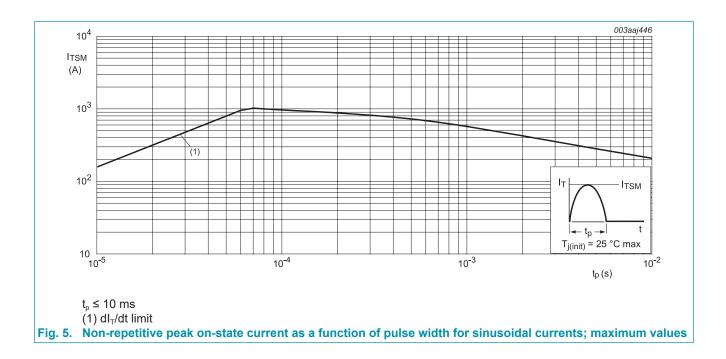


f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 6	-	-	1.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

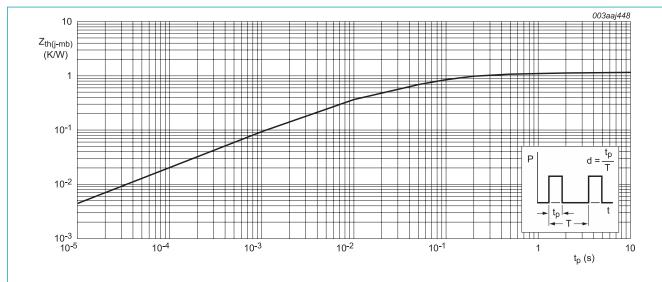
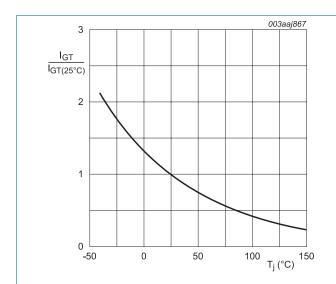


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

# 10. Characteristics

**Table 7. Characteristics** 

	Tidiacteristics			1		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
$I_{\rm GT}$	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	-	4.5	32	mA
$I_{L}$	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	21	60	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$	-	16	40	mA
$V_T$	on-state voltage	I <sub>T</sub> = 32 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A;} T_j = 25 \text{ °C; } Fig. 11$	-	0.7	1.3	V
		$V_D = 400V; I_T = 0.1 A; T_j = 150 °C$	0.2	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C	-	0.2	1	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 800 V; T <sub>j</sub> = 150 °C	-	0.2	1	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 402 V; T <sub>j</sub> = 150 °C;exponential waveform; gate open circuit	1000	-	-	V/µs
		$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = 800 \text{ V}; I_G = 100 \text{ mA};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C}$	-	-	2	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM}$ = 536 V; $T_{j}$ = 125 °C; $I_{TM}$ = 20 A; $V_{R}$ = 25 V; $(dI_{T}/dt)_{M}$ = 30 A/μs; $dV_{D}/dt$ = 50 V/μs; $R_{GK(ext)}$ = 100 $\Omega$ ; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	70	-	μs





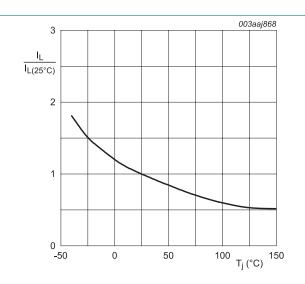


Fig. 8. Normalized latching current as a function of junction temperature

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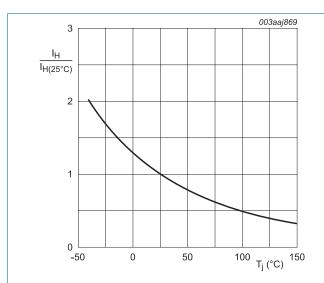
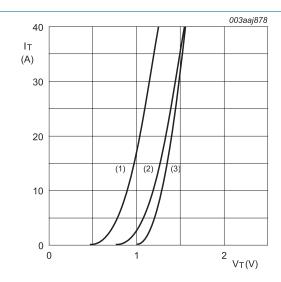


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0$  = 1.0485 V;  $R_s$  = 0.0133 Ω (1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

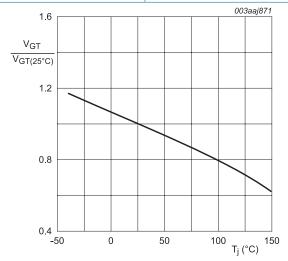
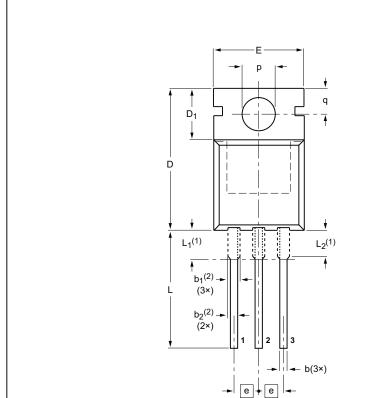


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

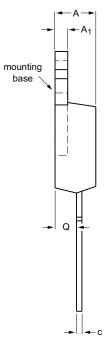
SOT78

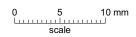
# 11. Package outline

Assembly factory: d & A



Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB





#### **DIMENSIONS** (mm are the original dimensions)

		•		-		•										
UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- Lead shoulder designs may vary.
   Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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